1. Scope :

This specification applies to PN silicon photodiode chips,
Device No. PD-0064

2. Structure :

2-1. Planar type : PN diode.
2-2. Electrodes :
Top side (Anode) : Aluminum alloy .
Back side (Cathode) : Gold alloy.

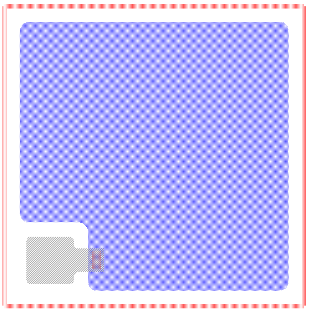
3. Size :

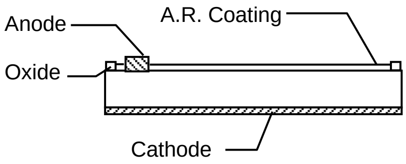
3-1. Chip size : 64 mils × 64 mils (1.63 mm × 1.63 mm).
3-2. Chip thickness : 16.0 ± 1.5 mils (0.400± 0.038 mm).
3-3. Active area : 56.7 mils × 56.7 mils (1.44 mm × 1.44 mm).
3-4. Bonding pad (Anode) : 10 mils × 10 mils (0.255 mm × 0.255mm).
3-5. Pattern drawing : Refer to the attached drawing.

4. Electro-optical characteristics (Ta = 25 ℃)

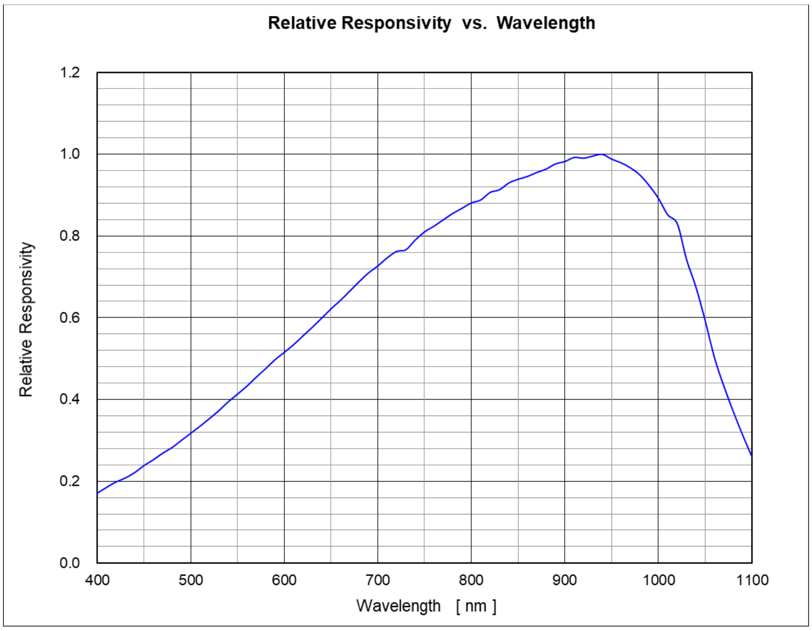
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
※Reverse dark Current	I_D	V_R=10V H=0mW/cm^2			10	nA
※Reverse breakdown voltage	$V_{(BR)R}$	I_R=100μA H=0mW/cm^2	60			V
Open circuit voltage	Voc	C_T=2870K H=5mW/cm^2		410		mV
Short circuit Current	Isc	C_T=2870K H=5mW/cm^2		17		μA
Reverse light current	I_L	V_R =5V C_T=2870K H=5mW/cm^2		17		μA
Total Capacitance	C_t	V_R =5V H=0mW/cm^2 f=1MHz		51		pF

※Based on 100% probing





5. Relative spectral responsivity



※Bare chip measured with integrating sphere, for reference only.